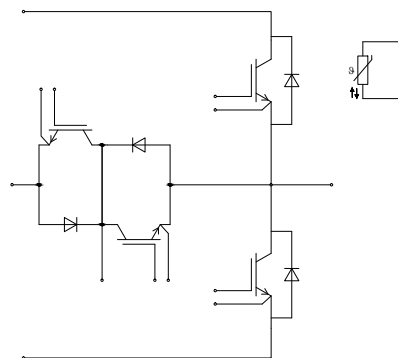
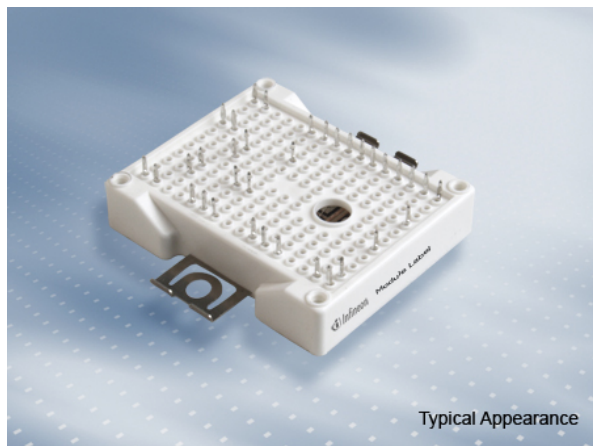


EasyPACK™ 模块 采用第二类中点钳位拓扑 (NPC2) 带有pressfit压接管脚和温度检测NTC / TIM
 EasyPACK™ module with active "Neutral Point Clamp 2" topology and PressFIT / NTC / TIM



$V_{CES} = 650V$
 $I_{C\ nom} = 125A / I_{CRM} = 250A$

典型应用

- 三电平应用
- 电机传动
- 太阳能应用
- UPS系统

电气特性

- 高速IGBT H3
- $T_{vj\ op} = 150^{\circ}C$

机械特性

- 2.5 kV 交流 1分钟 绝缘
- 集成NTC温度传感器
- PressFIT 压接技术
- 符合RoHS
- 预涂导热介质

Typical Applications

- 3-level-applications
- Motor drives
- Solar applications
- UPS systems

Electrical Features

- High speed IGBT H3
- $T_{vj\ op} = 150^{\circ}C$

Mechanical Features

- 2.5 kV AC 1min insulation
- Integrated NTC temperature sensor
- PressFIT contact technology
- RoHS compliant
- Pre-applied Thermal Interface Material

Module Label Code

Barcode Code 128



DMX - Code



Content of the Code

Content of the Code	Digit
Module Serial Number	1 - 5
Module Material Number	6 - 11
Production Order Number	12 - 19
Datecode (Production Year)	20 - 21
Datecode (Production Week)	22 - 23

IGBT, T1 / T4 / IGBT, T1 / T4

最大额定值 / Maximum Rated Values

集电极 - 发射极电压 Collector-emitter voltage	$T_{vj} = 25^{\circ}\text{C}$	V_{CES}	650	V
集电极电流 Implemented collector current		I_{CN}	225	A
连续集电极直流电流 Continuous DC collector current	$T_H = 95^{\circ}\text{C}, T_{vj\max} = 175^{\circ}\text{C}$	$I_{C\text{nom}}$	125	A
集电极重复峰值电流 Repetitive peak collector current	$t_p = 1\text{ms}$	I_{CRM}	450	A
栅极 - 发射极峰值电压 Gate-emitter peak voltage		V_{GES}	+/-20	V

特征值 / Characteristic Values

		min.	typ.	max.	
集电极 - 发射极饱和电压 Collector-emitter saturation voltage	$I_C = 125\text{A}, V_{GE} = 15\text{V}$ $I_C = 125\text{A}, V_{GE} = 15\text{V}$ $I_C = 125\text{A}, V_{GE} = 15\text{V}$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	$V_{CE\text{sat}}$	1,40 1,45 1,45	1,65 V V V
栅极阈值电压 Gate threshold voltage	$I_C = 3,60\text{mA}, V_{CE} = V_{GE}, T_{vj} = 25^{\circ}\text{C}$		$V_{G\text{Eth}}$	5,05	5,80 6,45 V
栅极电荷 Gate charge	$V_{GE} = -15\text{V} \dots +15\text{V}$		Q_G	2,40	μC
内部栅极电阻 Internal gate resistor	$T_{vj} = 25^{\circ}\text{C}$		$R_{G\text{int}}$	0,0	Ω
输入电容 Input capacitance	$f = 1\text{MHz}, T_{vj} = 25^{\circ}\text{C}, V_{CE} = 25\text{V}, V_{GE} = 0\text{V}$		C_{ies}	14,0	nF
反向传输电容 Reverse transfer capacitance	$f = 1\text{MHz}, T_{vj} = 25^{\circ}\text{C}, V_{CE} = 25\text{V}, V_{GE} = 0\text{V}$		C_{res}	0,42	nF
集电极-发射极截止电流 Collector-emitter cut-off current	$V_{CE} = 650\text{V}, V_{GE} = 0\text{V}, T_{vj} = 25^{\circ}\text{C}$		I_{CES}		1,0 mA
栅极-发射极漏电流 Gate-emitter leakage current	$V_{CE} = 0\text{V}, V_{GE} = 20\text{V}, T_{vj} = 25^{\circ}\text{C}$		I_{GES}		100 nA
开通延迟时间(电感负载) Turn-on delay time, inductive load	$I_C = 125\text{A}, V_{CE} = 400\text{V}$ $V_{GE} = \pm 15\text{V}$ $R_{G\text{on}} = 10\Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	$t_{d\text{on}}$	0,06 0,07 0,07	μs μs μs
上升时间(电感负载) Rise time, inductive load	$I_C = 125\text{A}, V_{CE} = 400\text{V}$ $V_{GE} = \pm 15\text{V}$ $R_{G\text{on}} = 10\Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	t_r	0,09 0,10 0,10	μs μs μs
关断延迟时间(电感负载) Turn-off delay time, inductive load	$I_C = 125\text{A}, V_{CE} = 400\text{V}$ $V_{GE} = \pm 15\text{V}$ $R_{G\text{off}} = 10\Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	$t_{d\text{off}}$	0,06 0,07 0,07	μs μs μs
下降时间(电感负载) Fall time, inductive load	$I_C = 125\text{A}, V_{CE} = 400\text{V}$ $V_{GE} = \pm 15\text{V}$ $R_{G\text{off}} = 10\Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	t_f	0,03 0,04 0,04	μs μs μs
开通损耗能量(每脉冲) Turn-on energy loss per pulse	$I_C = 125\text{A}, V_{CE} = 400\text{V}, L_S = 25\text{nH}$ $V_{GE} = \pm 15\text{V}, di/dt = 1500\text{A}/\mu\text{s} (T_{vj} = 150^{\circ}\text{C})$ $R_{G\text{on}} = 10\Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	E_{on}	8,50 10,0 10,5	mJ mJ mJ
关断损耗能量(每脉冲) Turn-off energy loss per pulse	$I_C = 125\text{A}, V_{CE} = 400\text{V}, L_S = 25\text{nH}$ $V_{GE} = \pm 15\text{V}, du/dt = 2900\text{V}/\mu\text{s} (T_{vj} = 150^{\circ}\text{C})$ $R_{G\text{off}} = 10\Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	E_{off}	4,40 5,20 5,80	mJ mJ mJ
短路数据 SC data	$V_{GE} \leq 15\text{V}, V_{CC} = 400\text{V}$ $V_{CE\text{max}} = V_{CES} - L_{S\text{CE}} \cdot di/dt$ $t_p \leq 0\mu\text{s}, T_{vj} = 150^{\circ}\text{C}$		I_{SC}	1300	A
结 - 散热器热阻 Thermal resistance, junction to heatsink	每个 IGBT / per IGBT valid with IFX pre-applied thermal interface material		R_{thJH}		0,364 K/W
在开关状态下温度 Temperature under switching conditions			$T_{vj\text{op}}$	-40	150 $^{\circ}\text{C}$

二极管, D2 / D3 / Diode, D2 / D3

最大额定值 / Maximum Rated Values

反向重复峰值电压 Repetitive peak reverse voltage	$T_{vj} = 25^{\circ}\text{C}$	V_{RRM}	650	V
正向电流 Implemented forward current		I_{FN}	100	A
连续正向直流电流 Continuous DC forward current		I_F	85	A
正向重复峰值电流 Repetitive peak forward current	$t_p = 1 \text{ ms}$	I_{FRM}	200	A
I^2t -值 I^2t - value	$V_R = 0 \text{ V}, t_p = 10 \text{ ms}, T_{vj} = 125^{\circ}\text{C}$ $V_R = 0 \text{ V}, t_p = 10 \text{ ms}, T_{vj} = 150^{\circ}\text{C}$	I^2t	850 800	A^2s A^2s

特征值 / Characteristic Values

				min.	typ.	max.	
正向电压 Forward voltage	$I_F = 85 \text{ A}, V_{GE} = 0 \text{ V}$ $I_F = 85 \text{ A}, V_{GE} = 0 \text{ V}$ $I_F = 85 \text{ A}, V_{GE} = 0 \text{ V}$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	V_F		1,55 1,50 1,45	2,00	V V V
反向恢复峰值电流 Peak reverse recovery current	$I_F = 85 \text{ A}, -di_F/dt = 1300 \text{ A}/\mu\text{s} (T_{vj}=150^{\circ}\text{C})$ $V_R = 400 \text{ V}$ $V_{GE} = -15 \text{ V}$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	I_{RM}		37,0 52,0 57,0		A A A
恢复电荷 Recovered charge	$I_F = 85 \text{ A}, -di_F/dt = 1300 \text{ A}/\mu\text{s} (T_{vj}=150^{\circ}\text{C})$ $V_R = 400 \text{ V}$ $V_{GE} = -15 \text{ V}$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	Q_r		2,50 4,80 5,60		μC μC μC
反向恢复损耗 (每脉冲) Reverse recovery energy	$I_F = 85 \text{ A}, -di_F/dt = 1300 \text{ A}/\mu\text{s} (T_{vj}=150^{\circ}\text{C})$ $V_R = 400 \text{ V}$ $V_{GE} = -15 \text{ V}$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	E_{rec}		0,24 0,65 0,79		mJ mJ mJ
结 - 散热器热阻 Thermal resistance, junction to heatsink	每个二极管 / per diode valid with IFX pre-applied thermal interface material		R_{thJH}			0,935	K/W
在开关状态下温度 Temperature under switching conditions			$T_{vj \text{ op}}$	-40		150	$^{\circ}\text{C}$

IGBT, T2 / T3 / IGBT, T2 / T3

最大额定值 / Maximum Rated Values

集电极 - 发射极电压 Collector-emitter voltage	$T_{vj} = 25^{\circ}\text{C}$	V_{CES}	650	V
集电极电流 Implemented collector current		I_{CN}	100	A
连续集电极直流电流 Continuous DC collector current	$T_H = 25^{\circ}\text{C}, T_{vj\max} = 175^{\circ}\text{C}$	$I_{C\text{nom}}$	85	A
集电极重复峰值电流 Repetitive peak collector current	$t_p = 1\text{ ms}$	I_{CRM}	200	A
栅极 - 发射极峰值电压 Gate-emitter peak voltage		V_{GES}	+/-20	V

特征值 / Characteristic Values

		min.	typ.	max.	
集电极 - 发射极饱和电压 Collector-emitter saturation voltage	$I_C = 85\text{ A}, V_{GE} = 15\text{ V}$ $I_C = 85\text{ A}, V_{GE} = 15\text{ V}$ $I_C = 85\text{ A}, V_{GE} = 15\text{ V}$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	$V_{CE\text{sat}}$	1,35 1,50 1,55	1,75 V V V
栅极阈值电压 Gate threshold voltage	$I_C = 1,60\text{ mA}, V_{CE} = V_{GE}, T_{vj} = 25^{\circ}\text{C}$		$V_{G\text{Eth}}$	4,95	5,80 6,45
栅极电荷 Gate charge	$V_{GE} = -15\text{ V} \dots +15\text{ V}$		Q_G	1,00	μC
内部栅极电阻 Internal gate resistor	$T_{vj} = 25^{\circ}\text{C}$		$R_{G\text{int}}$	2,0	Ω
输入电容 Input capacitance	$f = 1\text{ MHz}, T_{vj} = 25^{\circ}\text{C}, V_{CE} = 25\text{ V}, V_{GE} = 0\text{ V}$		C_{ies}	6,20	nF
反向传输电容 Reverse transfer capacitance	$f = 1\text{ MHz}, T_{vj} = 25^{\circ}\text{C}, V_{CE} = 25\text{ V}, V_{GE} = 0\text{ V}$		C_{res}	0,19	nF
集电极-发射极截止电流 Collector-emitter cut-off current	$V_{CE} = 650\text{ V}, V_{GE} = 0\text{ V}, T_{vj} = 25^{\circ}\text{C}$		I_{CES}		1,0 mA
栅极-发射极漏电流 Gate-emitter leakage current	$V_{CE} = 0\text{ V}, V_{GE} = 20\text{ V}, T_{vj} = 25^{\circ}\text{C}$		I_{GES}		100 nA
开通延迟时间(电感负载) Turn-on delay time, inductive load	$I_C = 85\text{ A}, V_{CE} = 400\text{ V}$ $V_{GE} = \pm 15\text{ V}$ $R_{G\text{on}} = 10\ \Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	$t_{d\text{on}}$	0,07 0,08 0,08	μs μs μs
上升时间(电感负载) Rise time, inductive load	$I_C = 85\text{ A}, V_{CE} = 400\text{ V}$ $V_{GE} = \pm 15\text{ V}$ $R_{G\text{on}} = 10\ \Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	t_r	0,04 0,05 0,05	μs μs μs
关断延迟时间(电感负载) Turn-off delay time, inductive load	$I_C = 85\text{ A}, V_{CE} = 400\text{ V}$ $V_{GE} = \pm 15\text{ V}$ $R_{G\text{off}} = 10\ \Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	$t_{d\text{off}}$	0,35 0,40 0,40	μs μs μs
下降时间(电感负载) Fall time, inductive load	$I_C = 85\text{ A}, V_{CE} = 400\text{ V}$ $V_{GE} = \pm 15\text{ V}$ $R_{G\text{off}} = 10\ \Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	t_f	0,05 0,10 0,10	μs μs μs
开通损耗能量(每脉冲) Turn-on energy loss per pulse	$I_C = 85\text{ A}, V_{CE} = 400\text{ V}, L_S = 25\text{ nH}$ $V_{GE} = \pm 15\text{ V}, di/dt = 1300\text{ A}/\mu\text{s} (T_{vj} = 150^{\circ}\text{C})$ $R_{G\text{on}} = 10\ \Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	E_{on}	4,80 7,10 7,60	mJ mJ mJ
关断损耗能量(每脉冲) Turn-off energy loss per pulse	$I_C = 85\text{ A}, V_{CE} = 400\text{ V}, L_S = 25\text{ nH}$ $V_{GE} = \pm 15\text{ V}, du/dt = 3500\text{ V}/\mu\text{s} (T_{vj} = 150^{\circ}\text{C})$ $R_{G\text{off}} = 10\ \Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	E_{off}	2,50 3,80 4,20	mJ mJ mJ
短路数据 SC data	$V_{GE} \leq 15\text{ V}, V_{CC} = 400\text{ V}$ $V_{CE\text{max}} = V_{CES} - L_{SCE} \cdot di/dt$ $t_p \leq 6\ \mu\text{s}, T_{vj} = 150^{\circ}\text{C}$		I_{SC}	500	A
结 - 散热器热阻 Thermal resistance, junction to heatsink	每个 IGBT / per IGBT valid with IFX pre-applied thermal interface material		$R_{th\text{JH}}$		0,802 K/W
在开关状态下温度 Temperature under switching conditions			$T_{vj\text{op}}$	-40	150 $^{\circ}\text{C}$

二极管, D1 / D4 / Diode, D1 / D4

最大额定值 / Maximum Rated Values

反向重复峰值电压 Repetitive peak reverse voltage	$T_{vj} = 25^{\circ}\text{C}$	V_{RRM}	650	V
正向电流 Implemented forward current		I_{FN}	225	A
连续正向直流电流 Continuous DC forward current		I_F	125	A
正向重复峰值电流 Repetitive peak forward current	$t_p = 1 \text{ ms}$	I_{FRM}	450	A
I ² t-值 I ² t - value	$V_R = 0 \text{ V}, t_p = 10 \text{ ms}, T_{vj} = 125^{\circ}\text{C}$ $V_R = 0 \text{ V}, t_p = 10 \text{ ms}, T_{vj} = 150^{\circ}\text{C}$	I^2t	3750 3500	A ² s A ² s

特征值 / Characteristic Values

		min.	typ.	max.	
正向电压 Forward voltage	$I_F = 125 \text{ A}, V_{GE} = 0 \text{ V}$ $I_F = 125 \text{ A}, V_{GE} = 0 \text{ V}$ $I_F = 125 \text{ A}, V_{GE} = 0 \text{ V}$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	V_F	1,35 1,25 1,20	1,55 V V V
反向恢复峰值电流 Peak reverse recovery current	$I_F = 125 \text{ A}, -di_F/dt = 1500 \text{ A}/\mu\text{s} (T_{vj}=150^{\circ}\text{C})$ $V_R = 400 \text{ V}$ $V_{GE} = -15 \text{ V}$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	I_{RM}	46,0 70,0 76,0	A A A
恢复电荷 Recovered charge	$I_F = 125 \text{ A}, -di_F/dt = 1500 \text{ A}/\mu\text{s} (T_{vj}=150^{\circ}\text{C})$ $V_R = 400 \text{ V}$ $V_{GE} = -15 \text{ V}$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	Q_r	6,40 12,5 14,5	μC μC μC
反向恢复损耗 (每脉冲) Reverse recovery energy	$I_F = 125 \text{ A}, -di_F/dt = 1500 \text{ A}/\mu\text{s} (T_{vj}=150^{\circ}\text{C})$ $V_R = 400 \text{ V}$ $V_{GE} = -15 \text{ V}$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	E_{rec}	1,30 2,90 3,30	mJ mJ mJ
结 - 散热器热阻 Thermal resistance, junction to heatsink	每个二极管 / per diode valid with IFX pre-applied thermal interface material		R_{thJH}		0,419 K/W
在开关状态下温度 Temperature under switching conditions			$T_{vj \text{ op}}$	-40	150 $^{\circ}\text{C}$

模块 / Module

绝缘测试电压 Isolation test voltage	RMS, $f = 50 \text{ Hz}, t = 1 \text{ min.}$	V_{ISOL}	2,5	kV
内部绝缘 Internal isolation	基本绝缘 (class 1, IEC 61140) basic insulation (class 1, IEC 61140)		Al_2O_3	
爬电距离 Creepage distance	端子至散热器 / terminal to heatsink 端子至端子 / terminal to terminal		11,5 6,3	mm
电气间隙 Clearance	端子至散热器 / terminal to heatsink 端子至端子 / terminal to terminal		10,0 5,0	mm
相对电痕指数 Comperative tracking index		CTI	> 200	

		min.	typ.	max.	
杂散电感, 模块 Stray inductance module		L_{sCE}	15	nH	
模块引线电阻, 端子-芯片 Module lead resistance, terminals - chip	$T_H = 25^{\circ}\text{C},$ 每个开关 / per switch	$R_{CC+EE'}$	1,25	m Ω	
储存温度 Storage temperature		T_{stg}	-40	125 $^{\circ}\text{C}$	
最高基板工作温度 Maximum baseplate operation temperature		T_{BPmax}		125 $^{\circ}\text{C}$	
Anpresskraft für mech. Bef. pro Feder mounting force per clamp		F	40	-	80 N
重量 Weight		G	41	g	

Der Strom im Dauerbetrieb ist auf 25A effektiv pro Anschlusspin begrenzt.
The current under continuous operation is limited to 25A rms per connector pin.
Lagerung und Transport von Modulen mit TIM => siehe AN2012-07
Storage and Shipment of modules with TIM => see AN2012-07

负温度系数热敏电阻 / NTC-Thermistor

特征值 / Characteristic Values

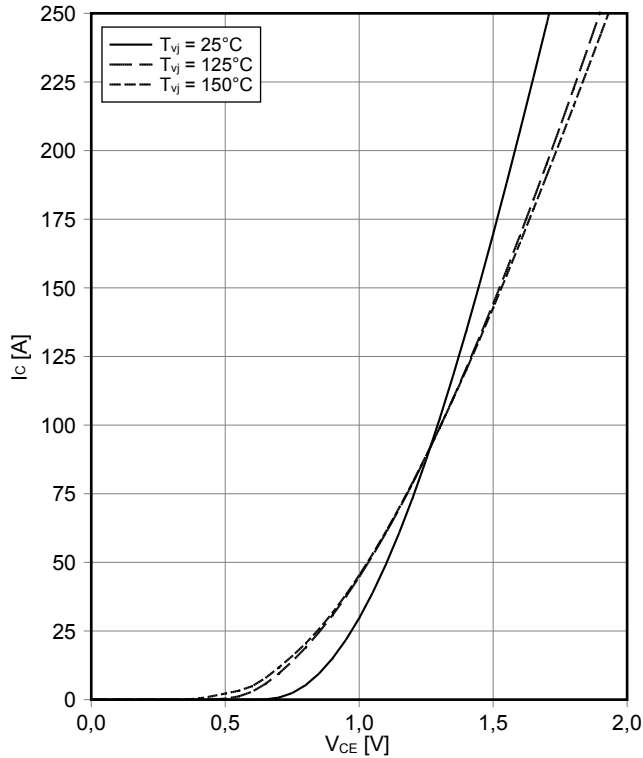
			min.	typ.	max.	
额定电阻值 Rated resistance	$T_{NTC} = 25^{\circ}\text{C}$	R_{25}		5,00		k Ω
R100 偏差 Deviation of R100	$T_{NTC} = 100^{\circ}\text{C}, R_{100} = 493 \Omega$	$\Delta R/R$	-5		5	%
耗散功率 Power dissipation	$T_{NTC} = 25^{\circ}\text{C}$	P_{25}			20,0	mW
B-值 B-value	$R_2 = R_{25} \exp [B_{25/50}(1/T_2 - 1/(298,15 \text{ K}))]$	$B_{25/50}$		3375		K
B-值 B-value	$R_2 = R_{25} \exp [B_{25/80}(1/T_2 - 1/(298,15 \text{ K}))]$	$B_{25/80}$		3411		K
B-值 B-value	$R_2 = R_{25} \exp [B_{25/100}(1/T_2 - 1/(298,15 \text{ K}))]$	$B_{25/100}$		3433		K

根据应用手册标定

Specification according to the valid application note.

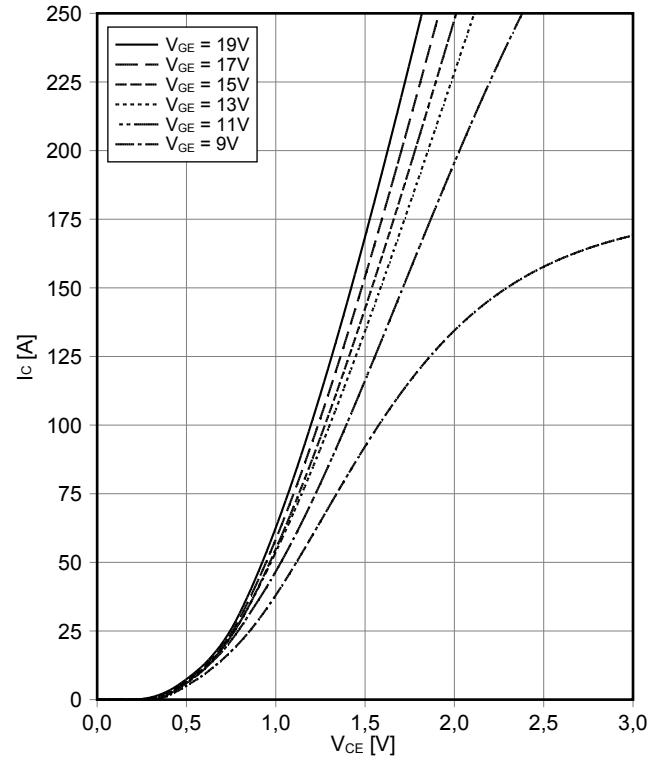
输出特性 IGBT, T1 / T4 (典型)
output characteristic IGBT, T1 / T4 (typical)

$I_C = f(V_{CE})$
 $V_{GE} = 15\text{ V}$



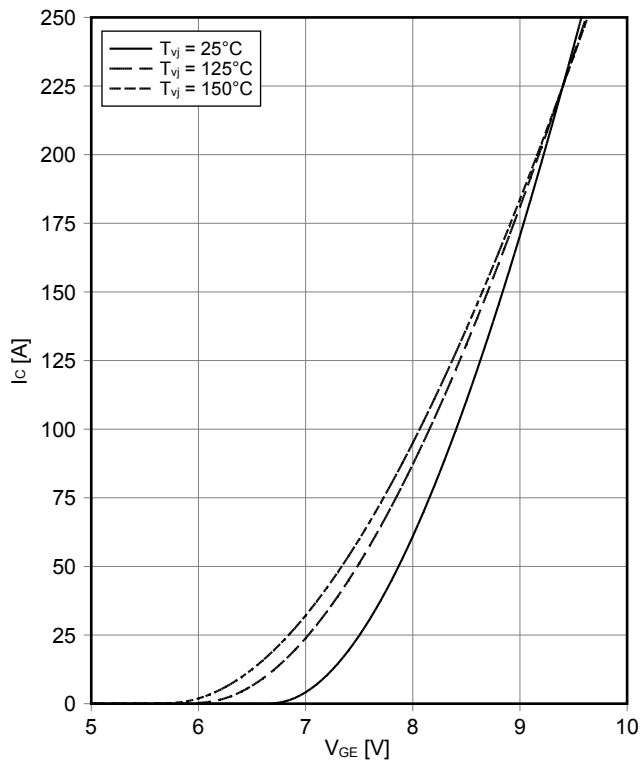
输出特性 IGBT, T1 / T4 (典型)
output characteristic IGBT, T1 / T4 (typical)

$I_C = f(V_{CE})$
 $T_{vj} = 150^\circ\text{C}$



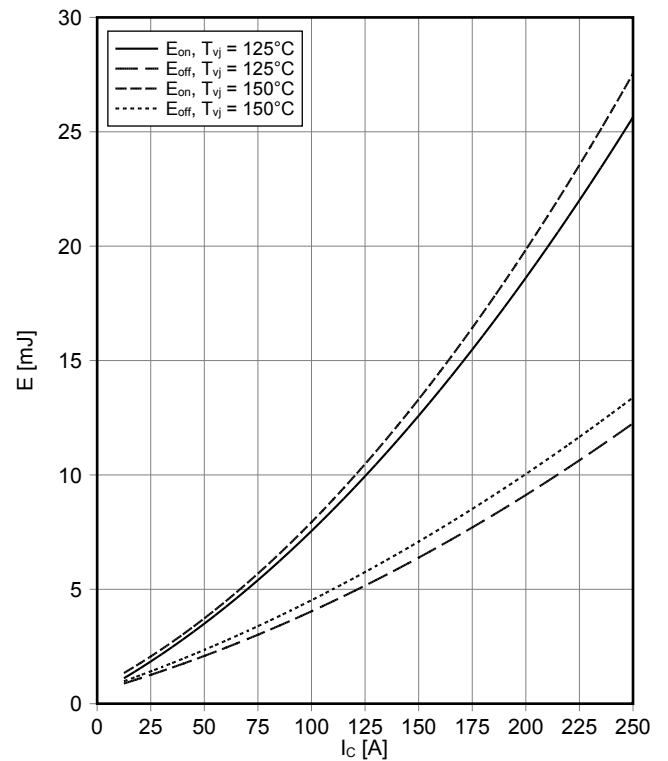
传输特性 IGBT, T1 / T4 (典型)
transfer characteristic IGBT, T1 / T4 (typical)

$I_C = f(V_{GE})$
 $V_{CE} = 20\text{ V}$



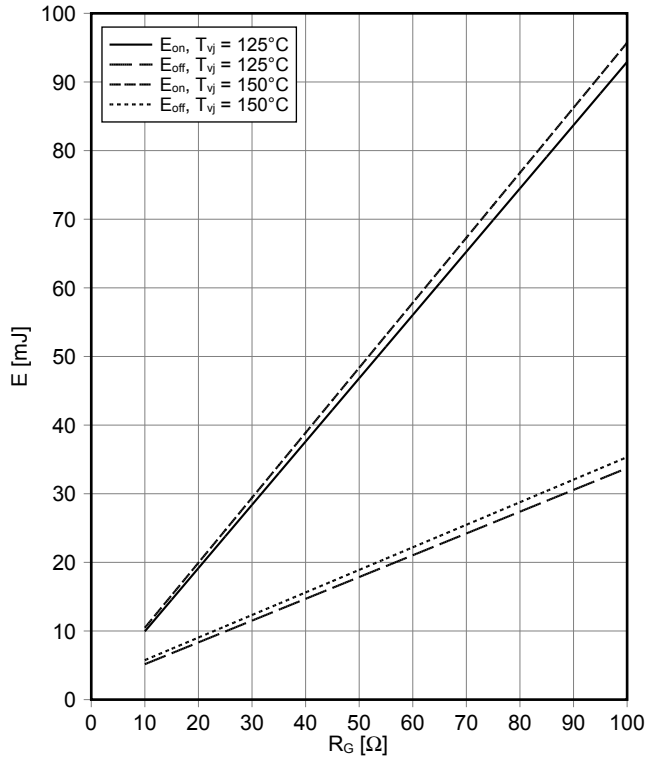
开关损耗 IGBT, T1 / T4 (典型)
switching losses IGBT, T1 / T4 (typical)

$E_{on} = f(I_C)$, $E_{off} = f(I_C)$
 $V_{GE} = \pm 15\text{ V}$, $R_{Gon} = 10\ \Omega$, $R_{Goff} = 10\ \Omega$, $V_{CE} = 400\text{ V}$

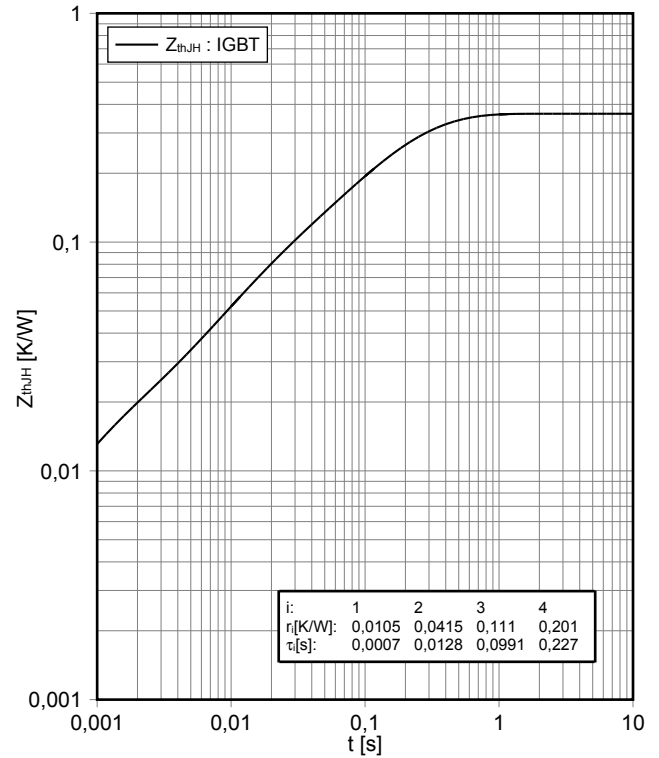


开关损耗 IGBT, T1 / T4 (典型)
switching losses IGBT, T1 / T4 (typical)

$E_{on} = f(R_G)$, $E_{off} = f(R_G)$
 $V_{GE} = \pm 15\text{ V}$, $I_C = 125\text{ A}$, $V_{CE} = 400\text{ V}$

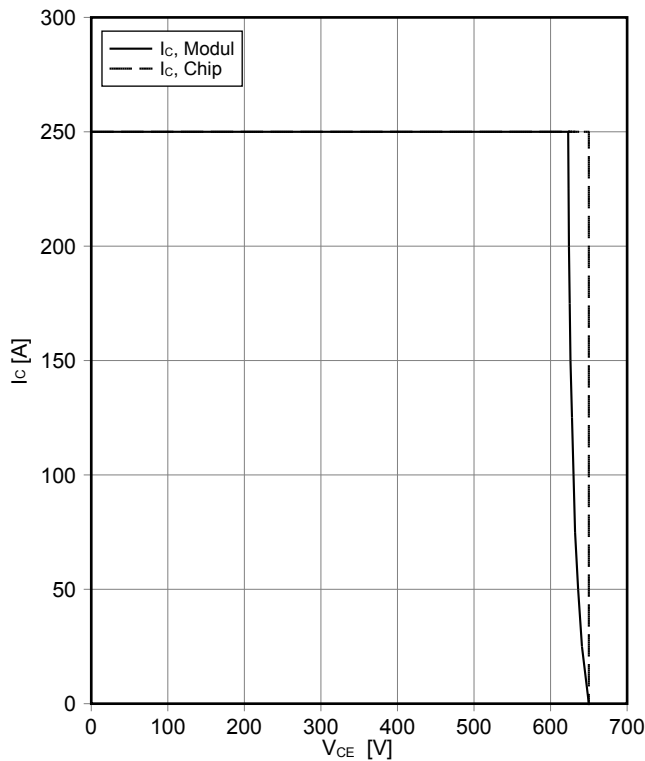


瞬态热阻抗 IGBT, T1 / T4
transient thermal impedance IGBT, T1 / T4
 $Z_{thJH} = f(t)$

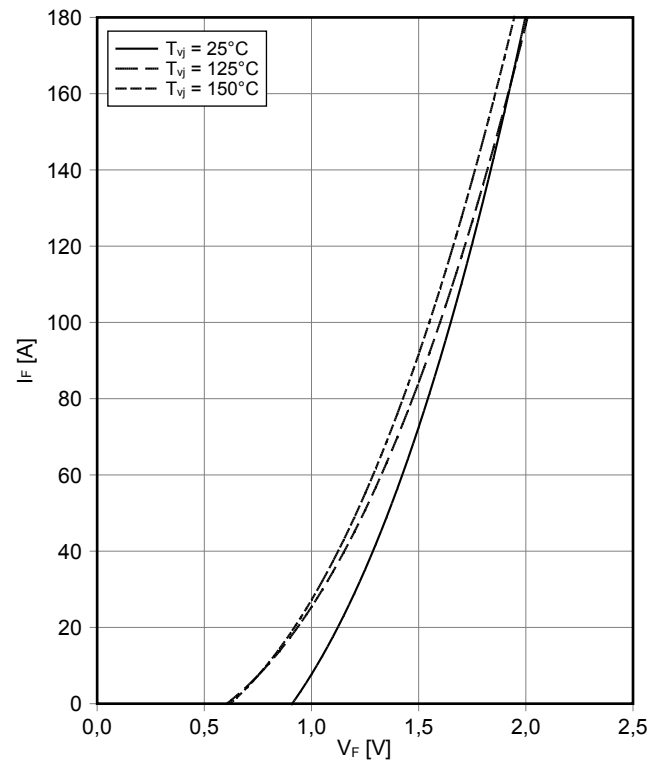


反偏安全工作区 IGBT, T1 / T4 (RBSOA)
reverse bias safe operating area IGBT, T1 / T4 (RBSOA)

$I_C = f(V_{CE})$
 $V_{GE} = \pm 15\text{ V}$, $R_{Goff} = 10\ \Omega$, $T_{vj} = 150^\circ\text{C}$

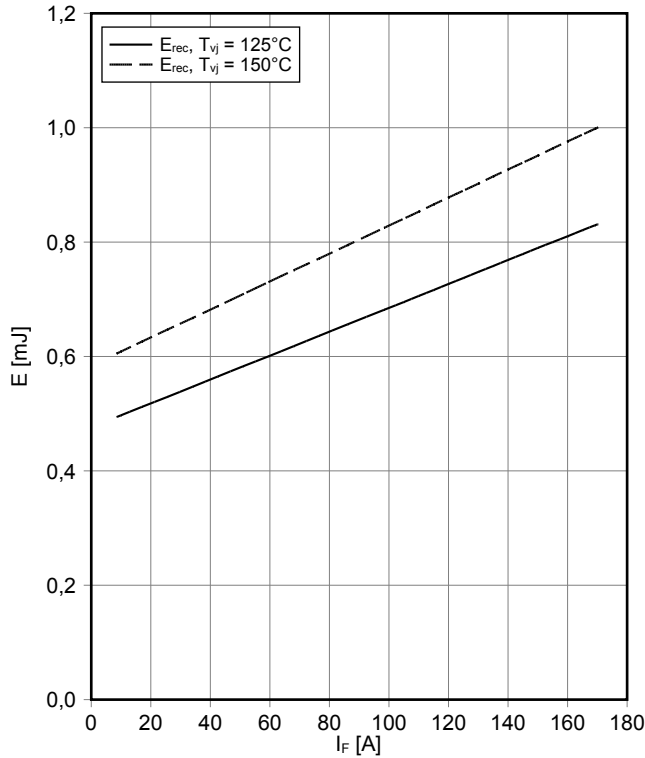


正向偏压特性 二极管, D2 / D3 (典型)
forward characteristic of Diode, D2 / D3 (typical)
 $I_F = f(V_F)$



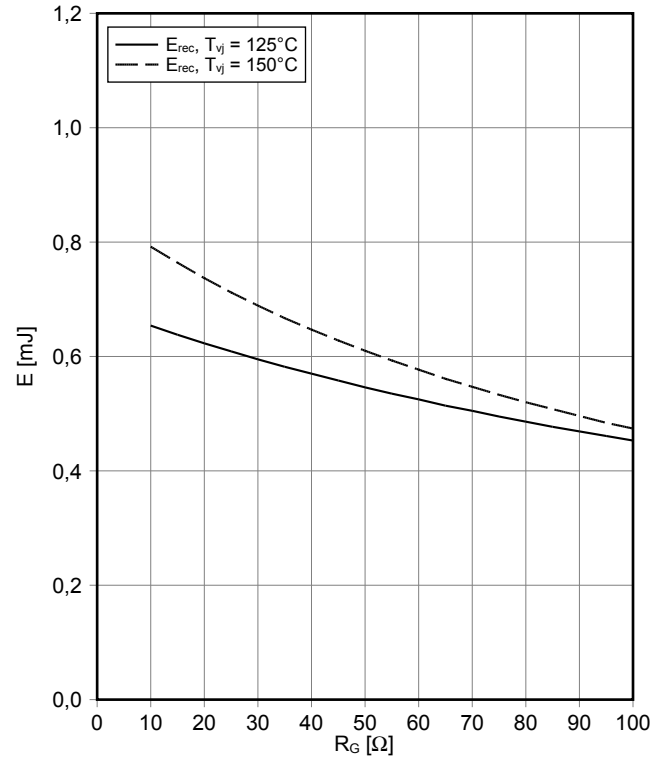
开关损耗 二极管, D2 / D3 (典型)
switching losses Diode, D2 / D3 (typical)

$E_{rec} = f(I_F)$
 $R_{Gon} = 10 \Omega, V_{CE} = 400 V$



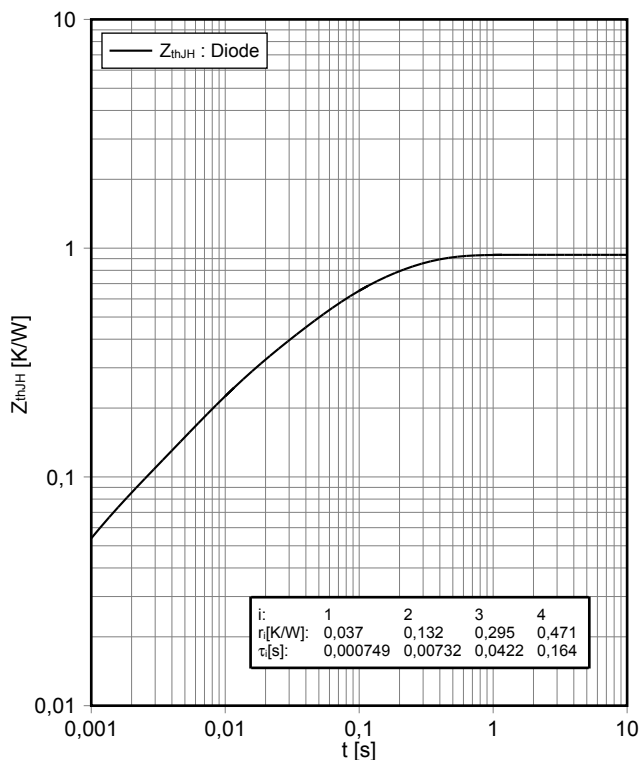
开关损耗 二极管, D2 / D3 (典型)
switching losses Diode, D2 / D3 (typical)

$E_{rec} = f(R_G)$
 $I_F = 85 A, V_{CE} = 400 V$



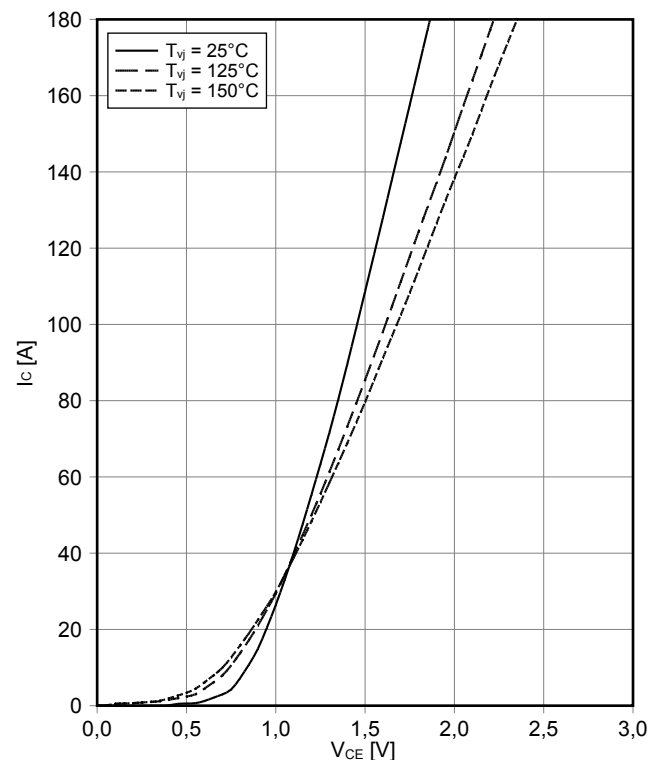
瞬态热阻抗 二极管, D2 / D3
transient thermal impedance Diode, D2 / D3

$Z_{thJH} = f(t)$



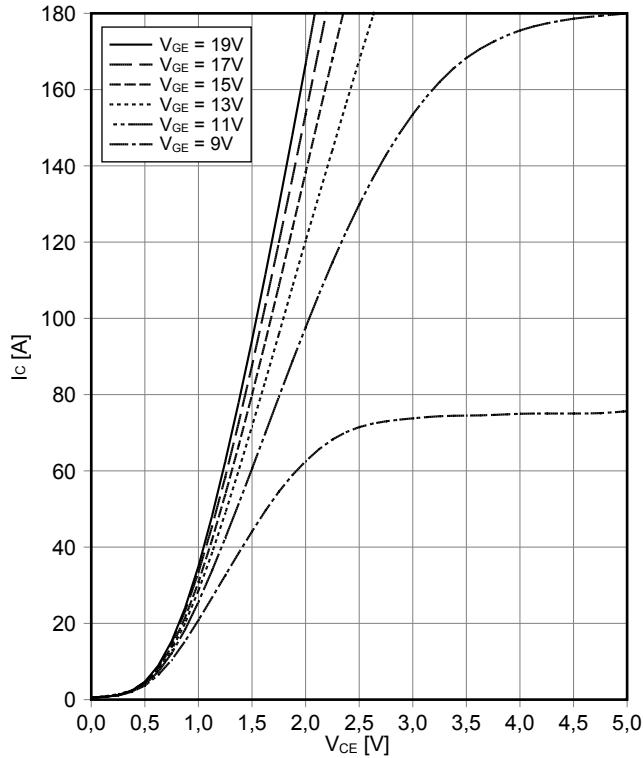
输出特性 IGBT, T2 / T3 (典型)
output characteristic IGBT, T2 / T3 (typical)

$I_C = f(V_{CE})$
 $V_{GE} = 15 V$



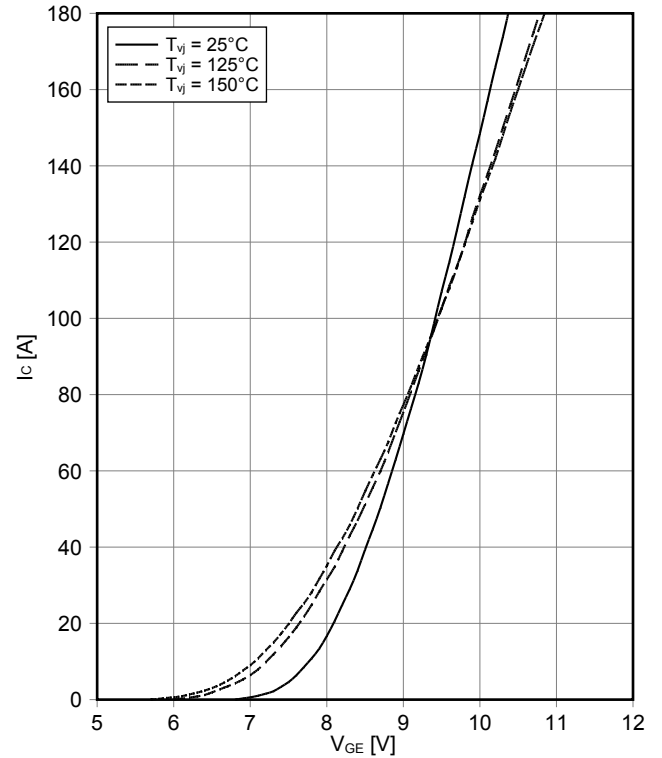
输出特性 IGBT, T2 / T3 (典型)
output characteristic IGBT, T2 / T3 (typical)

$I_C = f(V_{CE})$
 $T_{vj} = 150^\circ\text{C}$



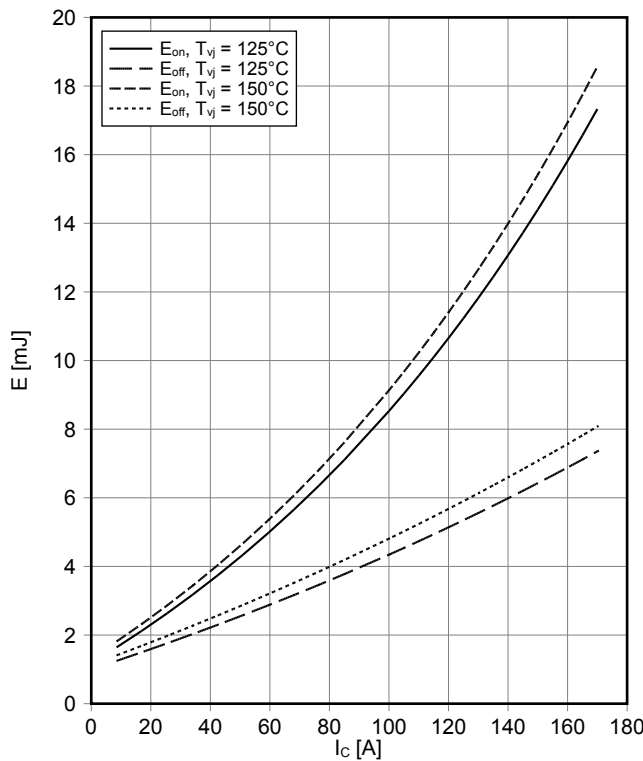
传输特性 IGBT, T2 / T3 (典型)
transfer characteristic IGBT, T2 / T3 (typical)

$I_C = f(V_{GE})$
 $V_{CE} = 20\text{ V}$



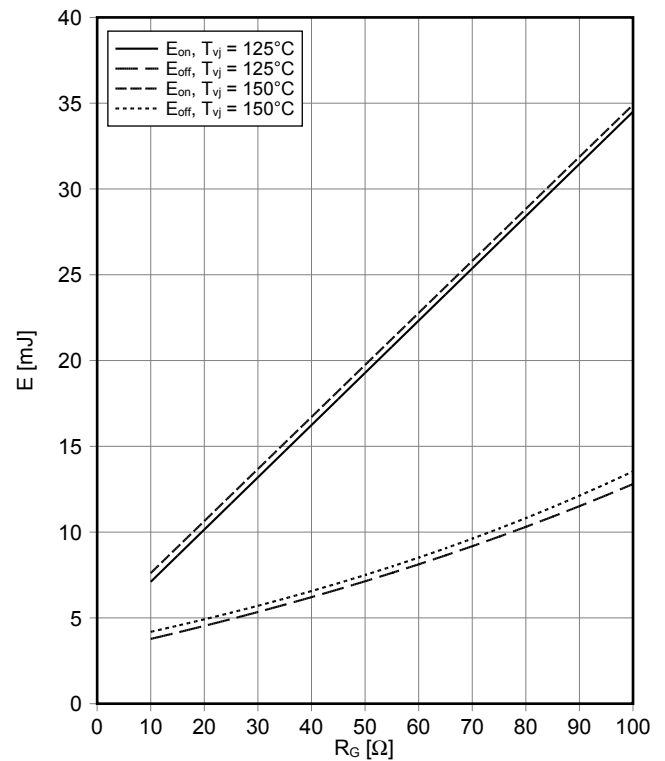
开关损耗 IGBT, T2 / T3 (典型)
switching losses IGBT, T2 / T3 (typical)

$E_{on} = f(I_C), E_{off} = f(I_C)$
 $V_{GE} = \pm 15\text{ V}, R_{Gon} = 10\ \Omega, R_{Goff} = 10\ \Omega, V_{CE} = 400\text{ V}$

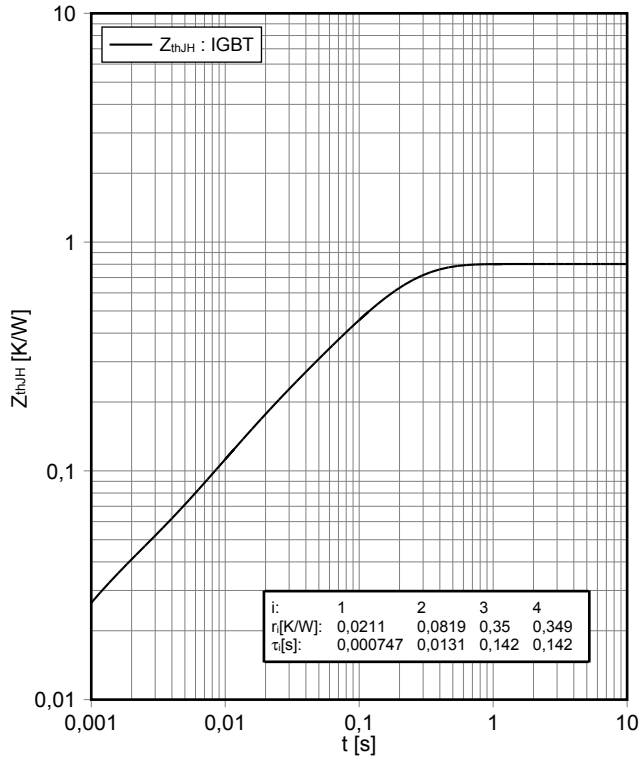


开关损耗 IGBT, T2 / T3 (典型)
switching losses IGBT, T2 / T3 (typical)

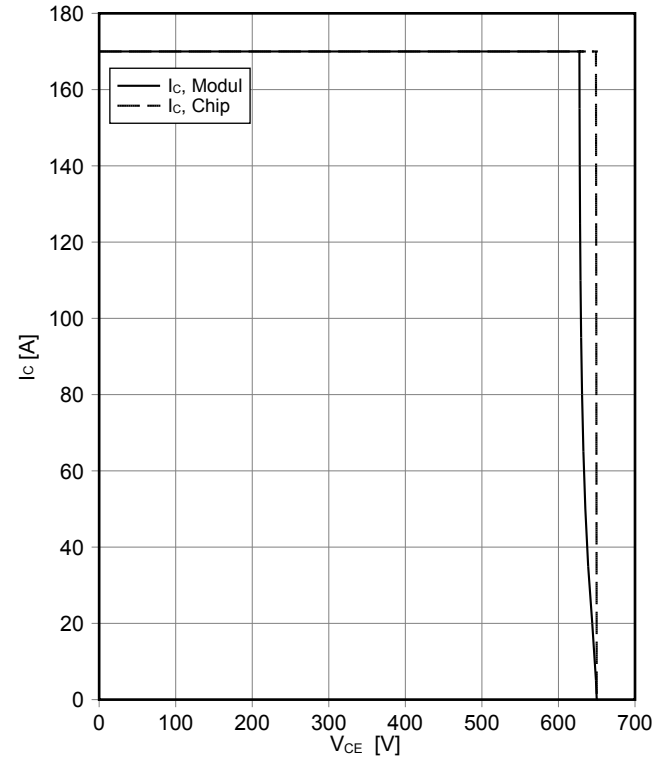
$E_{on} = f(R_G), E_{off} = f(R_G)$
 $V_{GE} = \pm 15\text{ V}, I_C = 85\text{ A}, V_{CE} = 400\text{ V}$



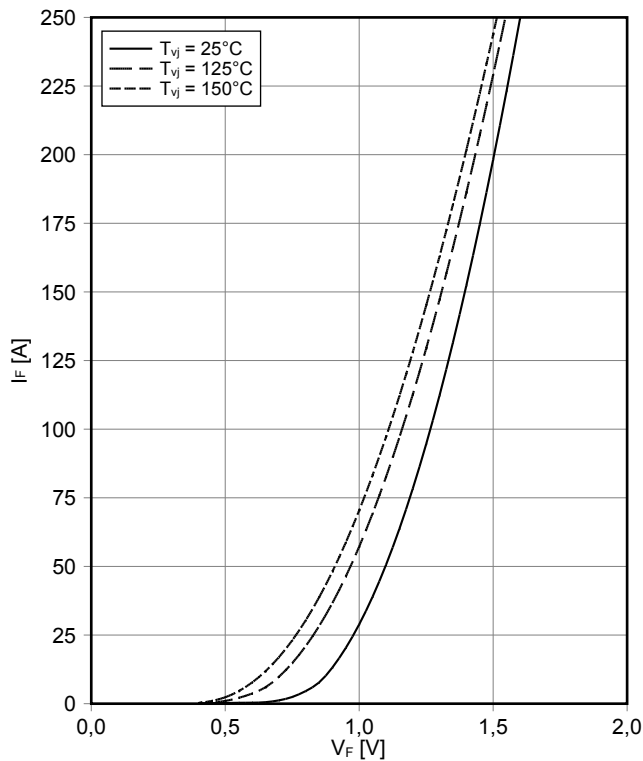
瞬态热阻抗 IGBT, T2 / T3
transient thermal impedance IGBT, T2 / T3
 $Z_{thJH} = f(t)$



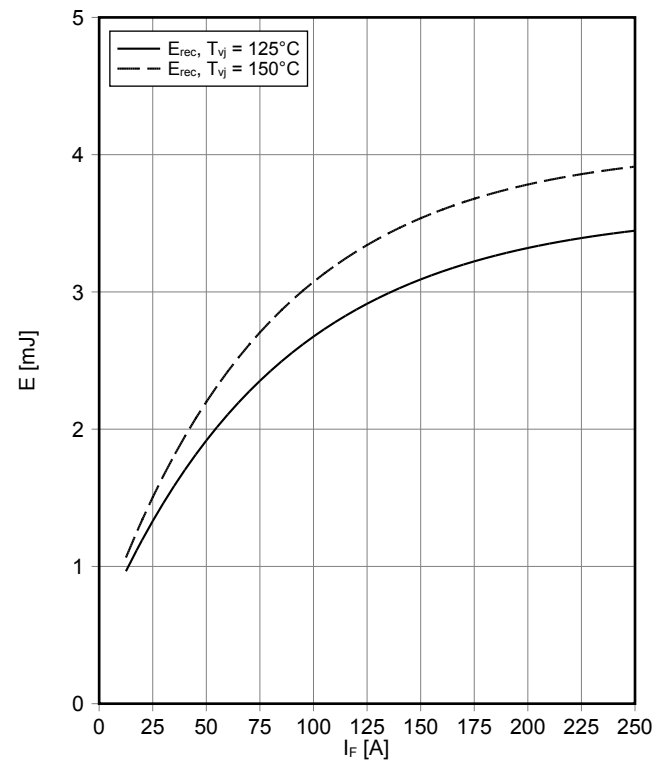
反偏安全工作区 IGBT, T2 / T3 (RBSOA)
reverse bias safe operating area IGBT, T2 / T3 (RBSOA)
 $I_C = f(V_{CE})$
 $V_{GE} = \pm 15 \text{ V}, R_{Goff} = 10 \Omega, T_{vj} = 150^\circ\text{C}$



正向偏压特性 二极管, D1 / D4 (典型)
forward characteristic of Diode, D1 / D4 (typical)
 $I_F = f(V_F)$

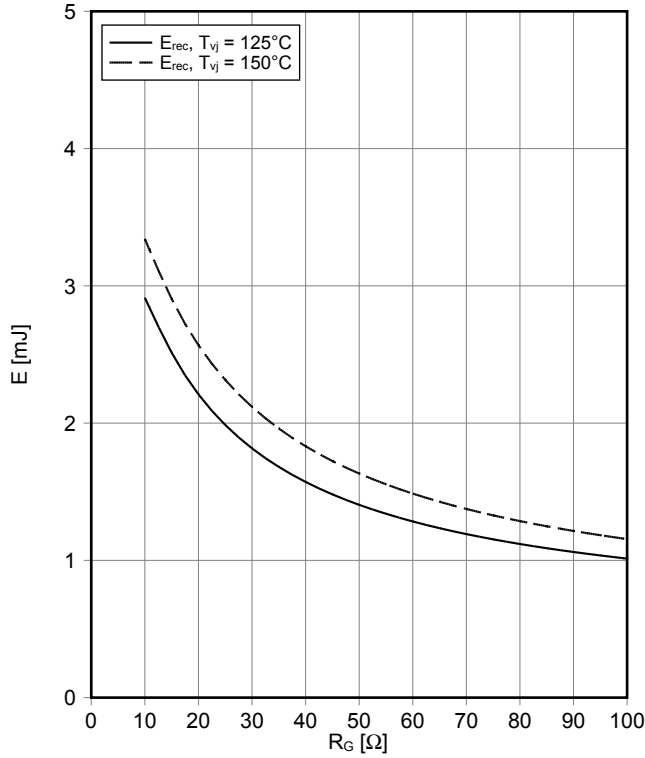


开关损耗 二极管, D1 / D4 (典型)
switching losses Diode, D1 / D4 (typical)
 $E_{rec} = f(I_F)$
 $R_{Gon} = 10 \Omega, V_{CE} = 400 \text{ V}$



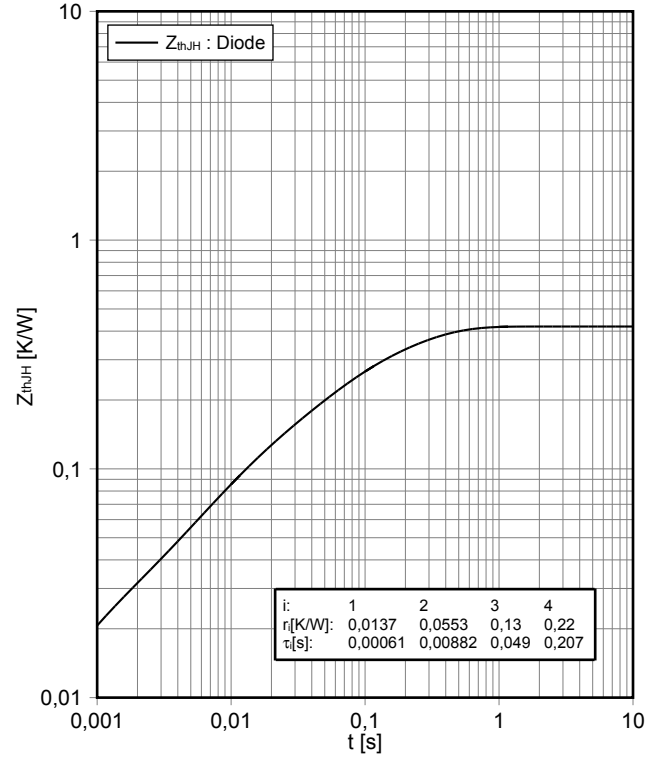
开关损耗 二极管, D1 / D4 (典型)
switching losses Diode, D1 / D4 (typical)

$E_{rec} = f(R_G)$
 $I_F = 125\text{ A}, V_{CE} = 400\text{ V}$

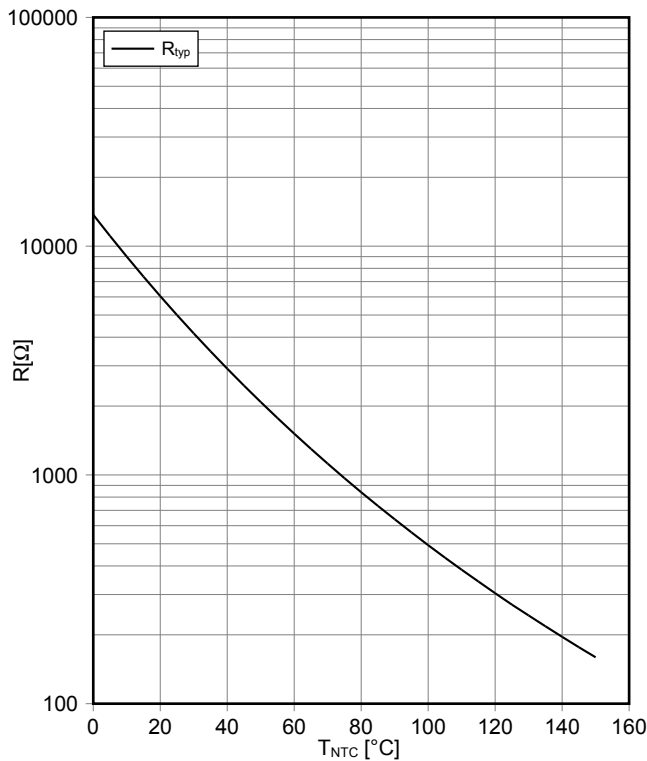


瞬态热阻抗 二极管, D1 / D4
transient thermal impedance Diode, D1 / D4

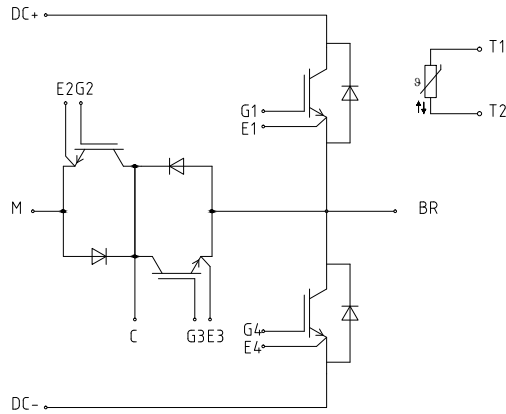
$Z_{thJH} = f(t)$



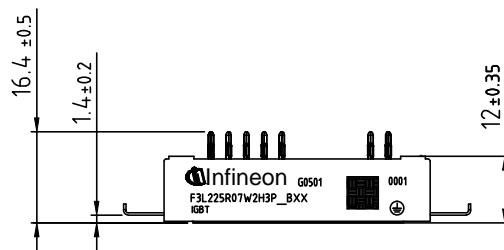
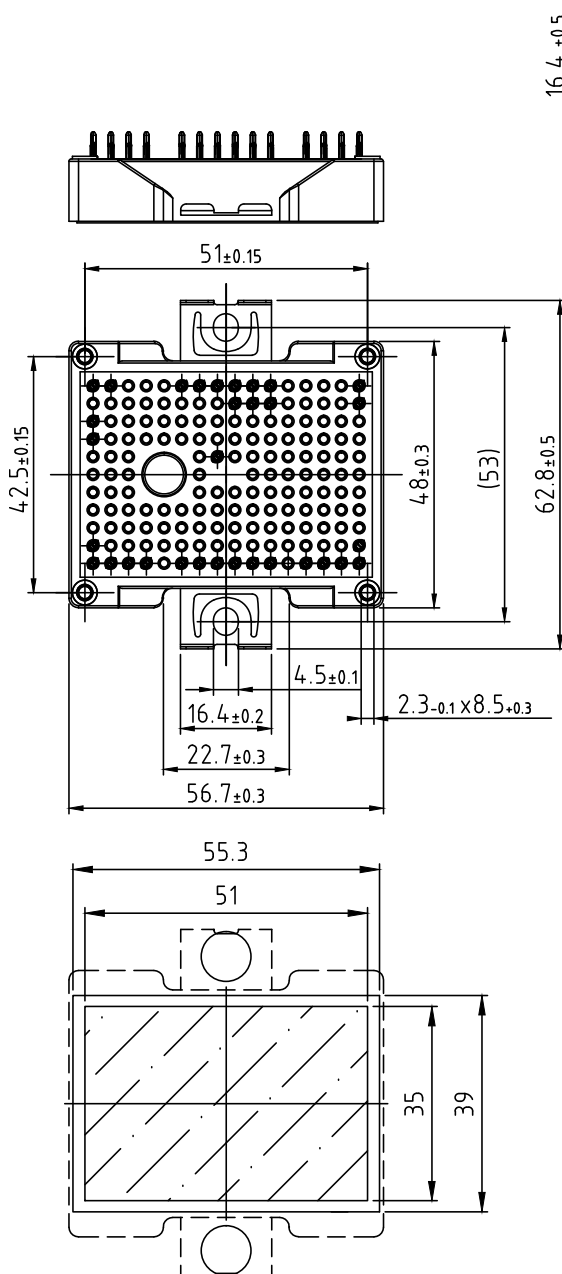
负温度系数热敏电阻 温度特性
NTC-Thermistor-temperature characteristic (typical)
 $R = f(T)$



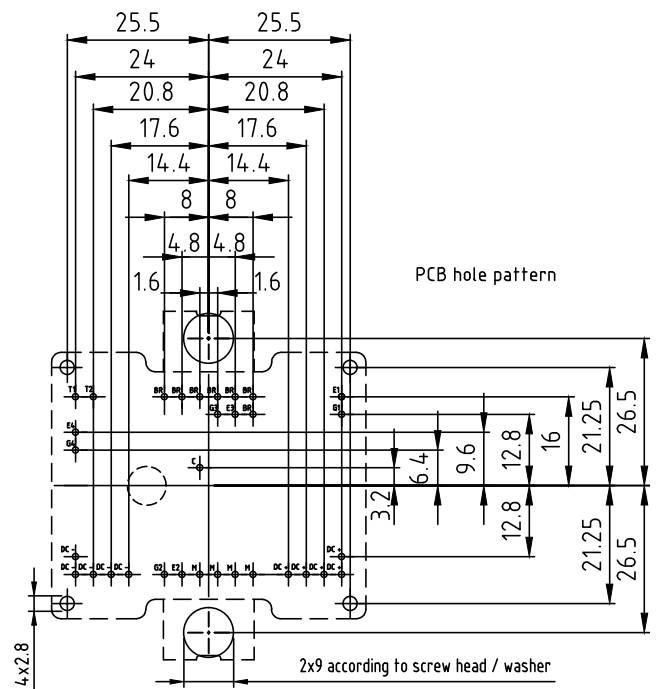
接线图 / Circuit diagram



封装尺寸 / Package outlines



- Pin-Grid 3.2mm
- Tolerance of PCB hole pattern $\varnothing 0.1$
- Hole specification for contacts see AN 2009-01:
Diameters of drill $\varnothing 1.15$ mm
and copper thickness in hole 25-50 μ m



restricted area for Thermal Interface Material

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